# **Dynamic-Offset Cancellation Techniques in CMOS**

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## **Motivation**

- Many analog circuits e.g. opamps, integrators, comparators, ADC and DAC stages etc. require amplifiers with offsets in the **microvolt** range
- Also, many sensors (e.g. thermopiles, bridges, halleffect sensors etc.) output DC signals that need to be processed with **microvolt** precision
- However, the offset of native CMOS amplifiers is typically in the **millivolt** range
- This tutorial will focus on **dynamic** offset-cancellation (DOC) techniques, with which offset can be reduced to the **microvolt** level.

## **Outline**

- Differential amplifiers Offset and 1/ *f* noise
- Trimming
- Dynamic Offset Cancellation
	- Auto-zeroing
	- $\circ$  Chopping
- Design of a CMOS temperature sensor
- •Summary
- References

#### **What is Offset?**



- $\bullet\;$  When the input of a REAL amplifier is shorted,  $\mathsf{V}_{\mathsf{out}}$   $\neq$  0!
- The **offset** V<sub>os</sub> is the input voltage required to make  $V_{\text{out}}$  = 0. It is typically in the range 100µV to 10mV.
- Note: In CMOS, input currents are usually negligible.

## **Amplifier Behaviour Near DC**

Characterized by

- •**Offset**
- •Drift
- •1/ *f* (flicker) noise
- Thermal noise
- $\bullet$ 1/ *f* corner frequency
- Errors due to finite CMRR and PSRR



## **Differential Amplifiers**

Differential amplifiers are often used to amplify DC signals.

Their balanced structure is

- Nominally offset free
- Rejects common-mode and power supply interference
- Easily realized in both CMOS and bipolar technologies



## **Offset in Differential Amplifiers**

Component mismatch e.g. R1<sup>≠</sup> R 2, M1<sup>≠</sup> M 2⇒ **offset**

Mismatch is mainly due to

- Doping variations
- Lithographic errors
- Packaging & local stress

All things being equal

- $\bullet$  Bipolar  $\Rightarrow$  V<sub>os</sub> ~ 0.1mV
- $\bullet$  CMOS  $\Rightarrow$  V $_{\text{os}}$  is 10 -100x worse!



### **What to Do?**

Offset and 1/ *f* noise are part of life!

But we can reduce offset "enough" by

- 1. Using "large" devices and good layout<sup>1</sup>  $\Rightarrow$  1mV
- 2. Trimming ⇒ 100µV
- 3. Dynamic offset-cancellation (DOC) techniques  $\Rightarrow$  1µV

DOC techniques also

- •Reduce drift and 1/ *f* noise
- •Improve PSRR and CMRR

## **Trimming**

- Low circuit complexity
- •Minimal effect on circuit bandwidth
- • Requires a memory element, e.g.
	- $\circ\,$  Fusible links (Zener diodes)
	- $\circ$  Laser-trimmed resistors
	- Floating gate MOSFETs
	- $\, \circ \,$  PROM
- Requires test infrastructure
- •Does not reduce drift or 1/ *f* noise
- • Poorly defined temp. dependence of MOSFETs  $\Rightarrow$  offset after trimming > 100µV over temp.

## **Dynamic Offset Cancellation (DOC)**

Two basic ideas $^{\mathsf{2}}$ 

- 1. Measure the offset somehow and then subtract it from the input signal  $\;\Rightarrow$  Auto-zeroing
- 2. Modulate the offset away from DC and then filter it out  $\Rightarrow$  Chopping

#### **DOC Techniques**

**Auto-zeroing**

Discrete time

Sample offset, then subtract.

**Chopping**

Continuous time

Modulate offset away from DC, then filter.

#### Switches required  $\;\Rightarrow$  CMOS or BiCMOS

## **DOC Techniques vs. Trimming**

- + reduction of offset and 1/ *f* noise
- + excellent stability (over temperature, time, supply and common-mode voltages)
- + no additional costs for testing
- possible bandwidth reduction
- increased circuit complexity
- aliasing & intermodulation issues

#### **Auto-zero Principle (1)**



Auto-zero phase

- $\bullet\quad$  S<sub>1</sub>, S<sub>2</sub> closed, S<sub>3</sub> open  $\Rightarrow$  V<sub>out</sub> = V<sub>os</sub>  $\Rightarrow$  offset stored on  $\text{C}_{\mathsf{az}}$
- Amplifier is unavailable

### **Auto-zero Principle (2)**



Amplification phase:

- $\bullet\;\;{\mathsf S}_1, \, {\mathsf S}_2$  open,  ${\mathsf S}_3$  closed  $\Rightarrow$   ${\mathsf V}_{\mathsf{in}}$  is amplified
- • *Finite* voltage gain A ⇒ error in sampled offset  $\Rightarrow$  input-referred residual offset V $_{\rm res}$  = V $_{\rm os}$ /(A+1)
- •Charge injection is also a problem …

## **Charge Injection (1)**



Consists of two components

- 1. Channel charge,  $Q_{ch}$ = WLC<sub>ox</sub>(V<sub>GS</sub>-V<sub>t</sub>)
- 2. Charge in the overlap capacitance between the gate and the source/drain  $\Rightarrow$  clock feed-through

Problematic when a MOSFET switches **OFF**.

## **Charge Injection (2)**



Error voltage  $\Delta {\rm V}_{\rm inj}$  depends on many factors $^{3,4}$ 

- •Source voltage and impedance
- •Transistor area (WL)
- •Clock amplitude & slew rate
- •Value of  $\text{C}_{\mathsf{az}}$  (larger values  $\Rightarrow$  smaller errors)
- • In a 0.7µm process, minimum size NMOS switch, 2.5V step & 10pF  $\Rightarrow$   $\Delta\mathsf{V}_{\mathsf{inj}}$  ~ 250µV

# **Mitigating Charge Injection (CI)**

- Use differential topologies  $\Rightarrow$  common-mode CI  $\Rightarrow$  1 $^{\rm st}$  order cancellation
- Use minimum size switches (subject to noise & BW requirements)
- For single-ended topologies dummy switches help3,4
- **But** area of main switch will be~2x minimum size  $\Rightarrow$  more CI  $\,$  $\Rightarrow$  limited benefit





## **Sampling the offset: kT/C noise**



- •Thermal noise of  $\mathsf{R}_{\mathsf{on}}$  is filtered by  $\mathsf{C}_{\mathsf{az}}$
- • When the switch is opened the instantaneous noise voltage is held on  $C_{27}$
- •Total noise power = kT/C $_{\rm az}$  (10pF @ 300K  $\Rightarrow$  20.3µV)
- •Large capacitance  $\Rightarrow$  accurate sampling of V<sub>os</sub>

## **Reducing Capacitor Size (1)**



$$
V_{res} = V_{os2}/(A_1A_2) + \Delta V_{inj}/A_1
$$

- •Offset of 1<sup>st</sup> amplifier is cancelled<sup>5,6</sup>
- •Gain of 1<sup>st</sup> amplifier reduces offset of 2<sup>nd</sup> amplifier
- •**But** too much gain ⇒ clipping!
- •Also reduces kT/C noise and charge injection errors
- $\Rightarrow$  Sampling capacitors can be smaller

## **Reducing Capacitor Size (2)**



Amplifier with an auxiliary input<sup>7,8</sup>

- $V_{res} \sim V_{os1}/(gm_2R) + V_{os2}/(gm_1R) + \Delta V_{inj}(gm_2/gm_1)$
- Large R and gm $_{2}$  << gm $_{1}$   $\Rightarrow$  low-offset and reduced kT/C noise and charge injection errors
- $\Rightarrow$  Sampling capacitors can be smaller

## **Residual Offset of Auto-zeroing**

Determined by

- Charge injection
- $\bullet~$  Leakage on  $\text{C}_{\mathsf{az}}$
- Finite amplifier gain

In practice

- Minimum size switches
- $\bullet$   $\,$   $\rm C_{az}$  as large as possible (sometimes external)
- Multi-stage amplifier topologies

Results in residual offsets of 1-10 $\mu$ V

## **Residual Noise of Auto-zeroing (1)**

 $V_{n,az}(f) = V_n(f)^*(1 - H(f))$ 

H(f) is the frequency response of the S&H

- $\textsf{H}(\textsf{f})=\textsf{sinc}(\pi\textsf{f}/\textsf{f}_{_{\textsf{S}}}) \Rightarrow \textsf{LPF}$
- $\Rightarrow$  1 H(f) is a HPF
- $\Rightarrow$  reduction of both offset and 1/ *f* noise
- $\Rightarrow$  but thermal noise will be (under) sampled



## **Residual Noise of Auto-zeroing (2)**



- •• Noise bandwidth B>f<sub>s</sub> (due to settling considerations)  $\Rightarrow$  input noise will be folded back (aliased) to DC
- $\bullet~$  The result is then LP filtered by the  ${\sf sinc}(\pi {\sf f}/{\sf f}_\text{s})$  function

## **Residual Noise of Auto-zeroing (3)**



- S&H with 100kHz clock & 50% duty-cycle
- •Noise aliasing  $\Rightarrow$  factor of 6 increase in LF noise!
- $\bullet$ Notches at multiples of **2**fclock due to 50% duty cycle 2
- •Sampled noise spectrum obtained with Spectre RF9,10

## **Residual Noise of Auto-zeroing (4)**



- Detailed analysis 2 ⇒ significant reduction of 1/ *f* noise **IF** f<sub>s</sub> >> 1/*f* corner frequency
- $\bullet$ Noise aliasing  $\Rightarrow$  LF power increased by the undersampling factor (USF) = 2B/f $_{\textrm{s}}$   $\Rightarrow$  factor 3 to 6 in volts

## **Ping-Pong Amplifier**

- Input signal "bounced" between two autozeroed amplifiers<sup>11,12</sup>
- Output V<sub>out</sub> is then a quasi-continuous signal
- $\bullet$  But switching spikes limit performance
- Randomized switching reduces spikes<sup>13</sup>



## **Offset Stabilization (OS)**



Low bandwidth, low offset compensating amplifier  $\Rightarrow$  Auto-zeroed or chopped

## **AZ Offset-Stabilized Amplifier**

- Auto-zeroed nulling amp cancels the offset of main amplifier<sup>14,15</sup>
- Continuous output and less spikes
- But poor overload performance, i.e. when  $\mathsf{V}_\text{\tiny{+}}-\mathsf{V}_\text{\tiny{-}} > \mathsf{V}_{\text{\tiny{OS}}}$
- Amplifier cannot be used as a comparator



#### **System-level Auto-zeroing**



- Phase 1:  $V_1 = A(V_{os} + V_{in})$
- •Phase 2:  $V_2 = AV_{\text{os}}$
- $\Rightarrow$  (V<sub>1</sub>-V<sub>2</sub>) = AV<sub>in</sub>
- •Offset stored in the digital domain
- •Widely used in instrumentation & measurement systems

## **Correlated Double Sampling (CDS)**



- Sometimes only a signal **difference** is required e.g. in image sensors
- Phase 1:  $V_1 = A(V_{in1} + V_{os})$
- Phase 2:  $\vee_2$  = A(  $\vee_{\text{in2}}$  +  $\vee_{\text{os}}$  )

$$
\Rightarrow (V_1 - V_2) = A(V_{in1} - V_{in2})
$$

• To maximize suppression of 1/f noise, the interval  $t_1 - t_2$ , should be as short as possible

#### **The 3 Signal Method**



- Phase 1:  $V_1 = A(V_{os} + V_{in})$
- Phase 2:  $\rm V_2$  = A(V $_{\rm os}$ + V $_{\rm ref}$ )
- $\bullet~$  Phase 3:  $\mathsf{V}_3$  = AV  $_{\mathsf{os}}$

$$
\Rightarrow V_{in} = V_{ref}(V_1 - V_3)/(V_2 - V_3)
$$

Requires a known reference voltage **and** a microprocessor to perform the division

## **Auto-Zeroing: Summary**

- Offsets in the range of 1-10µV can be achieved
- No loss of bandwidth with appropriate amplifier topologies (ping-pong, offset-stabilization)
- Sampled data technique  $\Rightarrow$  kT/C noise is an issue
- $\bullet~$  Noise aliasing will occur  $\Rightarrow$  increased LF noise
- DOC technique of choice in sampled-data systems e.g. switched-capacitor filters, ADCs etc.

## **Chopping Principle**



Signal is modulated, amplified and then demodulated<sup>16</sup>

- **+** Output signal is continuously available
- **-**- Low-pass filter required

#### **Square-wave Modulation**



- Easily generated modulating signal
- $\bullet$ Modulator is a simple polarity-reversing switch
- $\bullet$ Switches are easily realized in CMOS

## **Chopping in the Time Domain**



- $\bullet\;\;{\rm V}_{\rm res} = 0$  **IF** duty-cycle of  ${\rm V}_{\rm ch}$  is exactly 50%  $\Rightarrow$  flip-flop
- $\bullet$  If  $\rm V_{os}^{}=10mV$  & f $\rm_{ch}^{}=50kHz,$  then 1ns skew  $\rm \Rightarrow V_{res}^{}=1\mu V$

## **Chopping in the Frequency Domain**



## **Residual Noise of Chopping**



- 1/ *f* noise is **completely** removed **IF**  $f_{\sf ch}$  > 1/*f* corner frequency
- $\bullet$ Significantly better than auto-zeroing!

#### **Bandwidth & Gain Accuracy**



- $\bullet~$  Limited BW  $\Rightarrow$  lower effective gain  $\mathsf{A}_{\mathsf{eff}}$  $\mathop{\mathsf{and}}$  chopping artifacts at even harmonics of f $_{\mathsf{ch}}$
- $A_{\text{eff}} = A (1-4\tau/T_{\text{ch}})$  for a 1<sup>st</sup> order LP filter, where BW = 1/2 $\pi$ τ and τ << T $_{\rm ch}$
- T<sub>ch</sub> / $\tau$  = 40  $\Rightarrow$  BW = 6.4f<sub>ch</sub>  $\Rightarrow$  10% gain error!

## **Chopper Opamp with Feedback**



- Feedback resistors  $\Rightarrow$  Accurate gain $^{17,18}$
- •To suppress  $\mathsf{V}_{\text{os}2}$ ,  $\mathsf{A}_1$  should have high gain
- •Miller capacitors  $\mathsf{C}_{\mathsf{m}}$  also suppress ripple
- •Minimum ripple  $\Rightarrow$  high chopping frequencies

## **Residual Offset of Chopping (1)**



- Due to mismatched charge injection and clock feedthrough at the input chopper<sup>19,20</sup>
- $\bullet$  Causes a typical offset of 1-10 $\mu$ V
- •Input spikes  $\Rightarrow$  bias current (typically 50pA)

## **Residual Offset of Chopping (2)**



- Residual offset $^2$  = 2f $_{\rm ch}$  V $_{\rm spike}$ τ
- $\bullet~$  Spike shape (τ) depends on source impedance e.g. feedback resistors around an opamp

## **Design Considerations**

Input chopper

- •Use minimum size switches
- •Good layout  $\Rightarrow$  symmetric, balanced clock coupling
- Ensure that switches "see" equal impedances
- Use a flip-flop to ensure an exact 50% duty-cycle

#### Chopping frequency  $f_{ch}$

- Higher than 1/ *f* noise corner frequency
- $\bullet~$  Not **too** high, as the residual offset increases with f $_{\mathsf{ch}}$

Amplifier BW >>  $\mathsf{f}_{\mathsf{ch}}$  to minimize gain errors

### **Band-Pass Filtering**



- Spike spectrum is "whiter" than that of modulated signal ⇒ BP filter will reduce **relative** spike amplitude19,21,22
- Clock frequency tracks BP filter's center frequency  $\Rightarrow$  low Q filter, Q ~ 5
- $\bullet$ Residual offset ~ 0.5 μV!

### **Delayed Demodulation**

- Optimal delay  $\sim 0.7\tau_{\rm spike}$
- •Tricky timing!
- Solution: clock and spikes delayed by identical amplifiers<sup>23</sup>
- $\bullet$ Residual offset  $\sim 1 \mu V$



## **Nested Chopping**



- •Inner HF chopper removes 1/ *f* noise
- •Outer LF chopper removes residual offset<sup>24,25</sup>
- •Residual offset ~ 100nV, but reduced bandwidth
- •Note: input choppers should not be merged!

## **Dead-Banding**



- •During dead-band amplifiers output is tri-stated<sup>26,27,28</sup>
- •Residual offset ~ 200nV!
- BUT loss of gain and aliasing due to S&H action  $\Rightarrow$  slightly worse noise performance

## **Precision V-I Converter**



- $\bullet~$  Front-end of a magnetic field sensor $^{29}$  with  $<$  50nV offset!
- •Fast output chopper implements dead-bands
- •During dead-bands, output current flows into a CM node
- •Slow output chopper implemented in ADC

## **Dealing with Spikes: Overview**

- $\bullet$ BP Filtering: ~ 0.5 μV offset, complex clock timing
- Delayed demodulation:  $\sim$  1  $\mu$ V offset, complex clock timing
- •Dead-banding: ~ 200nV offset, wide BW
- •Nested chopping: ~ 100nV offset, but limited BW

Last two techniques represent best compromise between offset magnitude and circuit complexity

## **Chopping Artifacts**



Modulated offset  $\Rightarrow$  chopping artifacts  $\;$ 

- •Can be removed by a low-pass filter
- $\bullet$  BUT analog filters with low cut-off frequencies are difficult to realize on chip

## **Auto-zeroing and Chopping**



- •Significantly improves LF noise performance<sup>30,31,42</sup>
- •Much less artifacts than with chopping alone
- 3  $\mu$ V offset & 20nV/ $\sqrt{Hz}$  demonstrated in a ping-pong amplifier<sup>30</sup>
- •Choosing  $f_{ch} = 2f_{az} \Rightarrow$  aliased noise has notch at DC

## **AC Coupling**



- AC coupling will block the amplifier's offset
- Alternatively, DC "servo" loop (shown) *inside* the choppers will also suppress the amplifier's offset $32,33$
- Note: DC servo loop *outside* the choppers results in a low-noise amplifier with a HPF characteristic<sup>33,34</sup>

## **Switched Capacitor Filter (1)**



- • Chopped offset is integrated & the triangular ripple is then sampled at the zero-crossings<sup>35</sup>
- •SC filter essentially eliminates residual ripple
- •Filter introduces delay and a (small) noise penalty

## **Switched Capacitor Filter (2)**



- • SC filters have been used in **true** chopper-stabilized opamps9,36
- $\bullet~$  Note: gm4 is not chopped  $\Rightarrow$  V $_{\sf res}$  > V $_{\sf os4}$ A $_{\sf gm4}$ /(A $_{\sf gm1}$ A $_{\sf gm2})$
- • Filter delay incorporated into a multi-path nested Miller compensation scheme

## **Digital Filtering**



- •Chopped signal is digitized
- •Demodulation is done digitally<sup>25,37</sup>
- • Chopper artifacts are removed by a digital LPF e.g. a sinc filter with notches at  $f_{ch}$

## **Dealing with Artifacts: Overview**

Reduce the amplifier's initial offset

- •Auto-zeroing and chopping: increased noise
- •DC servo: still requires some analog filtering
- Switched capacitor filtering

Digital Filtering

- Very low cut-off frequencies can be realized
- $\bullet$  Decimation filter of a ΣΔ ADC can be used to remove chopper artifacts  $\Rightarrow$  no extra overhead

## **Chopping: Summary**

- •Offsets in the range of 50nV-10µV can be achieved
- Fundamental loss of bandwidth (unless offset-stabilized topologies can be used)
- Eliminates 1/ *f* noise, noise floor set by thermal noise
- $\bullet$  DOC technique of choice when noise or offset performance is paramount e.g. in biomedical amplifiers, low-power opamps, smart sensors etc.

#### **State-of-the-Art Opamps**



**\***Conditionally stable

## Design of a CMOS Temp. Sensor<sup>40,41</sup>

- Why CMOS 'smart' temperature sensors? + digital interface + low cost
- But accuracy is a problem! Only  $\pm2.0^{\circ}$ C from –55°C to 125 ° $^{\circ}{\rm C}$
- By comparison: class-A Pt100 achieves  $\pm 0.5^{\circ}\text{C}$  in the same temp. range
- Goal: ±0.1°C from –55°C to 125°Cwith single temperature calibration only

## **Operating Principle**



• Substrate PNPs generate:

 $\Delta V_{BE^-}$  proportional to absolute temp. (PTAT)  $V_{BF}$ complementary to absolute temp. (CTAT)

• Ratiometric measurement: *BE BE BE REFTEMP*  $V_{RF} + \alpha \cdot \Delta V$ *V V V*  $+ \, \alpha \cdot \Delta$  $\mu = \frac{V_{\text{TEMP}}}{V} = \frac{\alpha \cdot \Delta}{V}$ 

#### **Block Diagram**



- ΣΔ modulator produces bitstream *bs* whose average is representation of temperature
- $\bullet \;\;$  <u>Offset</u> in  $\Delta V_{BE}$  read-out results in errors of ~10°C/mV  $\Rightarrow$  offset << 10 $\mu$ V required for error << 0.1°C
- $\bullet~$  Spread of  $\mathcal{V}_{BE}$  and bias-current ratio are mitigated by trimming and DEM respectively<sup>40,41</sup>
- • Bitstream is filtered and scaled by decimation filter to produce binary reading in °C

#### **Charge Balancing in** ΣΔ



- Every clock cycle, either 16·∆V<sub>BE</sub> (bs=0) or  $-V_{BE}$  (bs=1) is input to the loopfilter
- $\bullet$ Resulting bitstream average μ:

$$
\mu \cdot V_{BE} = (1 - \mu) \cdot 16 \cdot \Delta V_{BE} \Rightarrow \mu = \frac{16 \cdot \Delta V_{BE}}{V_{BE} + 16 \cdot \Delta V_{BE}} = \frac{16 \cdot \Delta V_{BE}}{V_{REF}}
$$
  
ISSCC 2007 K.A.A. Makinwa 61

#### **Switched-Capacitor 1st Integrator**



- PNPs  $Q_L$  and  $Q_R$  generate  $\Delta\,V_{BE}$  (bs=0) or  $\,V_{BE}$  (bs=1)
- $C_{\text{S1}}$ - $C_{\text{S8}}$   $\Rightarrow$  gain of 1 or 16 (with 2 integration cycles)
- ISSCC 2007 K.A.A. Makinwaa 62 • Correlated double-sampling (CDS) used to sample  $\Delta$   $V_{BE}$  *or*  $V_{BE}$  *and cancel opamp's offset and 1/f noise*

#### $\boldsymbol{\Delta}$ *VBE* **Sampling (***bs***=0)**



- •PNPs biased at 1:5 current ratio
- • $\Delta\mathsf{V}_{\mathsf{BE},\mathsf{RL}}$  **and** offset sampled on 8 sampling capacitors
- •Minimum size NMOS switches + 5pF caps
- ISSCC 2007 K.A.A. Makinwaa 63  $\Rightarrow$  residual offset ~ 10 $\mu$ V  $\Rightarrow$  too high  $\;$

#### $\boldsymbol{\Delta}$ *VBE* **Integration (***bs***=0)**



- $\bullet$  Bias currents are swapped  $\Rightarrow$  integrated charge: 8  $\cdot$   $C_{\textrm{S}}\cdot$   $(\Delta V_{BE,RL}$  +  $\Delta V_{BE,LR})$
- $\bullet$   $\,$  2 integration cycles in 1  $\Sigma\Delta$  cycle  $\Rightarrow$  total charge: 16  $\cdot$   $C_{\text{S}}\cdot$   $(\Delta V_{BE,RL}$  +  $\Delta V_{BE,LR})$

# *VBE* **Sampling (***bs***=1)**



- • $Q_L$  biased at programmable current  $I_{trim}$
- $\bullet$  $\bullet~~ -V_{BEL}$  and offset sampled on 1 sampling capacitor

# *VBE* **Integration (***bs***=1)**



- $\bullet$   $\,$   $\,I_{trim}$  swapped to  $\, \mathrm{Q}_{R} \,$  $\Rightarrow$  total charge:  $C_\mathcal{S}\cdot(V_{BEL}+V_{BER})$
- compare with 16  $\cdot$   $C_{\textrm{S}}\cdot$   $(\Delta V_{BE,RL}$  +  $\Delta V_{BE,LR})$  $\Rightarrow$  effective 16x gain for  $\Delta\mathsf{V}_{\!B\!E}$

#### **Chopped** ΣΔ **Modulator**



ISSCC 2007 K.A.A. Makinwaa 67 Offset after CDS >10 μV ⇒ input, output **and** modulator state are chopped 2x per conversion  $\Rightarrow$  sub- $\mu\mathsf{V}$  offset

## **Chip Micrograph**



- • $4.5\mathsf{mm}^2$  in 0.7 μm CMOS
- Off-chip decimation filter removes chopper residuals
- • Supply voltage: 2.5..5.5V
- •Supply current: 75µA

#### **Measurement Results**



24 samples from 1 batchInaccuracy (±3 <sup>σ</sup>) after trimming at 30°C: ±0.03°C 30°C  $\pm 0.1^{\circ}$ C –55..125 $^{\circ}$ C

World's most accurate CMOS temp sensor!

## **Summary**

- Offset and 1/*f* are part of life!
- Trimming
	- $\circ$  reduces offset but not 1/*f* noise
	- $\circ\,$  no loss of bandwidth
- Auto-zeroing
	- $\circ~$  Reduces 1/*f* noise, but sampling  $\Rightarrow$  noise aliasing
	- $\circ$  Indirect loss of bandwidth
- Chopping
	- eliminates 1/ *f* noise
	- $\circ$  Direct loss of bandwidth
- $\bullet~$  Nested DOC techniques  $\Rightarrow$  sub-microvolt offset

